

L Number	Hits	Search Text	DB	Time stamp
1	319170	liquid near6 crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:28
2	28927	passivation near6 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:31
3	3858	(liquid near6 crystal) near6 seal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:33
4	2540	remov\$3 near6 (passivation near6 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:35
5	0	((liquid near6 crystal) near6 seal) near6 (remov\$3 near6 (passivation near6 (film or layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:35
6	50	((liquid near6 crystal) near6 seal) and (remov\$3 near6 (passivation near6 (film or layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:41
7	94095	active near6 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:43
8	4382	remov\$3 near6 (active near6 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:46
9	0	((liquid near6 crystal) near6 seal) near6 (remov\$3 near6 (active near6 layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:46
10	10	((liquid near6 crystal) near6 seal) and (remov\$3 near6 (active near6 layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:47
11	60	349/153 and (passivation near6 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:48
12	14	349/190 and (passivation near6 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 13:48

13	65	(349/153 and (passivation near6 (film or layer))) or (349/190 and (passivation near6 (film or layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:14
14	336102	(drive or driving or wiring) near6 circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:08
15	2224	remov\$3 near6 ((drive or driving or wiring) near6 circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:10
16	0	((liquid near6 crystal) near6 seal) near6 (remov\$3 near6 ((drive or driving or wiring) near6 circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:11
17	4	((liquid near6 crystal) near6 seal) and (remov\$3 near6 ((drive or driving or wiring) near6 circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:11
18	5	(passivation near6 (film or layer)) near6 ((liquid near6 crystal) near6 seal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:45
19	9872	data near6 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:49
20	234975	data near6 line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:51
21	0	((liquid near6 crystal) near6 seal) near6 (data near6 pad) near6 (data near6 line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 14:51
22	30	((liquid near6 crystal) near6 seal) and (data near6 pad) and (data near6 line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:01
23	69735	gate near6 insulat\$3 near6 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:04
24	80460	capacit\$3 near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:07
25	22238	pixel near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:09

26	1046	auxiliary near6 capacit\$3 near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:12
27	100	(pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:14
28	46	((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode)) and @py<2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:24
29	60	(gate near6 insulat\$3 near6 (layer or film)) and (capacit\$3 near6 electrode) and (pixel near6 electrode) and (auxiliary near6 capacit\$3 near6 electrode) and ((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:24
30	25	((gate near6 insulat\$3 near6 (layer or film)) and (capacit\$3 near6 electrode) and (pixel near6 electrode) and (auxiliary near6 capacit\$3 near6 electrode) and ((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode))) and @py<2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:47
31	2	5739880.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:50
32	76	(gate near6 insulat\$3 near6 (layer or film)) near6 above near6 (capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:54
33	0	(auxiliary near6 capacit\$3 near6 electrode) near6 above near6 (active near6 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:55
34	1	(auxiliary near6 capacit\$3 near6 electrode) near6 over near6 (active near6 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 16:20
35	219279	semiconductor near6 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:58
36	0	(auxiliary near6 capacit\$3 near6 electrode) near6 (above or over) near6 (semiconductor near6 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:58
37	2	(semiconductor near6 layer) near6 (under or below) near6 (auxiliary near6 capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 15:59
38	23	(semiconductor near6 layer) near6 (auxiliary near6 capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 16:12

39	166	(capacit\$3 near6 electrode) near6 (above or over) near6 (semiconductor near6 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 16:13
40	1	((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode)) and ((capacit\$3 near6 electrode) near6 (above or over) near6 (semiconductor near6 layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 16:16
41	20	(passivation near6 (film or layer)) and ((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/09 16:21